

# Silizium-PIN-Fotodiode Silicon PIN Photodiode

## SFH 206 K



### Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 400 nm bis 1100 nm
- Kurze Schaltzeit (typ. 20 ns)
- 5-mm-Plastikbauform im LED-Gehäuse
- Auch gegurtet lieferbar

### Anwendungen

- Computer-Blitzlichtgeräte
- Lichtschranken für Gleich- und Wechsellichtbetrieb
- Industrieelektronik
- „Messen/Steuern/Regeln“

### Features

- Especially suitable for applications from 400 nm to 1100 nm
- Short switching time (typ. 20 ns)
- 5 mm LED plastic package
- Also available on tape and reel

### Applications

- Computer-controlled flashes
- Photointerrupters
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code
SFH 206 K	Q62702-P129

**Grenzwerte**  
**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Löttemperatur (Lötstelle 2 mm vom Gehäuse entfernt bei Lötzeit $t \leq 3$ s) Soldering temperature in 2 mm distance from case bottom ( $t \leq 3$ s)	$T_S$	230	°C
Sperrspannung Reverse voltage	$V_R$	32	V
Verlustleistung, $T_A = 25$ °C Total power dissipation	$P_{tot}$	150	mW

**Kennwerte** ( $T_A = 25$  °C, Normlicht A,  $T = 2856$  K)  
**Characteristics** ( $T_A = 25$  °C, standard light A,  $T = 2856$  K)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Fotoempfindlichkeit, $V_R = 5$ V Spectral sensitivity	$S$	80 ( $\geq 50$ )	nA/lx
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\ max}$	850	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von $S_{max}$ Spectral range of sensitivity $S = 10\%$ of $S_{max}$	$\lambda$	400 ... 1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	$A$	7.00	mm <sup>2</sup>
Abmessung der bestrahlungsempfindlichen Fläche Dimensions of radiant sensitive area	$L \times B$ $L \times W$	2.65 × 2.65	mm × mm
Abstand Chipoberfläche zu Gehäuseoberfläche Distance chip front to case surface	$H$	1.2 ... 1.4	mm
Halbwinkel Half angle	$\varphi$	± 60	Grad deg.
Dunkelstrom, $V_R = 10$ V Dark current	$I_R$	2 ( $\leq 30$ )	nA
Spektrale Fotoempfindlichkeit, $\lambda = 850$ nm Spectral sensitivity	$S_\lambda$	0.62	A/W

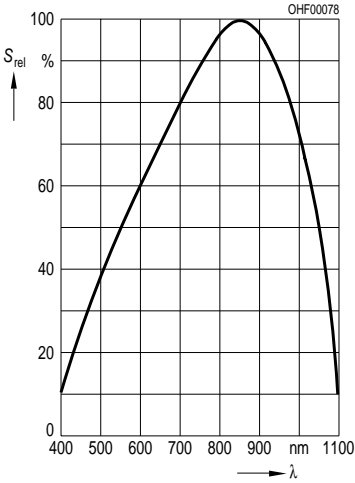
**Kennwerte** ( $T_A = 25\text{ °C}$ , Normlicht A,  $T = 2856\text{ K}$ )

**Characteristics** ( $T_A = 25\text{ °C}$ , standard light A,  $T = 2856\text{ K}$ ) (cont'd)

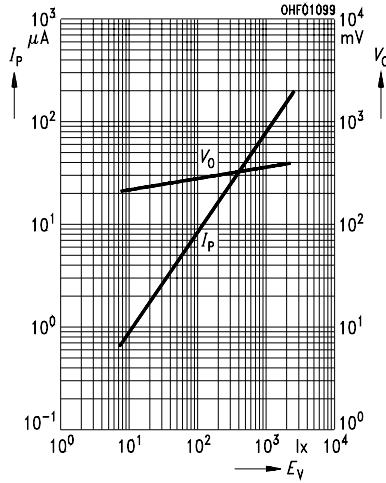
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Quantenausbeute, $\lambda = 850\text{ nm}$ Quantum yield	$\eta$	0.90	<u>Electrons</u> Photon
Leerlaufspannung, $E_V = 1000\text{ lx}$ Open-circuit voltage	$V_O$	365 ( $\geq 310$ )	mV
Kurzschlußstrom, $E_V = 1000\text{ lx}$ Short-circuit current	$I_{SC}$	80	$\mu\text{A}$
Anstiegs- und Abfallzeit des Fotostromes Rise and fall time of the photocurrent $R_L = 50\ \Omega$ ; $V_R = 5\text{ V}$ ; $\lambda = 850\text{ nm}$ ; $I_p = 800\ \mu\text{A}$	$t_r, t_f$	20	ns
Durchlaßspannung, $I_F = 100\text{ mA}$ , $E = 0$ Forward voltage	$V_F$	1.3	V
Kapazität, $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$ Capacitance	$C_0$	72	pF
Temperaturkoeffizient von $V_O$ Temperature coefficient of $V_O$	$TC_V$	-2.6	mV/K
Temperaturkoeffizient von $I_{SC}$ Temperature coefficient of $I_{SC}$	$TC_I$	0.18	%/K
Rauschäquivalente Strahlungsleistung Noise equivalent power $V_R = 10\text{ V}$ , $\lambda = 850\text{ nm}$	$NEP$	$4.2 \times 10^{-14}$	$\frac{\text{W}}{\sqrt{\text{Hz}}}$
Nachweisgrenze, $V_R = 10\text{ V}$ , $\lambda = 850\text{ nm}$ Detection limit	$D^*$	$6.3 \times 10^{12}$	$\frac{\text{cm} \times \sqrt{\text{Hz}}}{\text{W}}$

**Relative Spectral Sensitivity**

$S_{rel} = f(\lambda)$



**Photocurrent  $I_P = f(E_V), V_R = 5 V$   
Open-Circuit Voltage  $V_O = f(E_V)$**



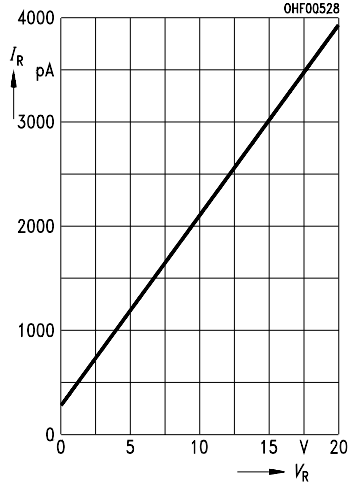
**Total Power Dissipation**

$P_{tot} = f(T_A)$



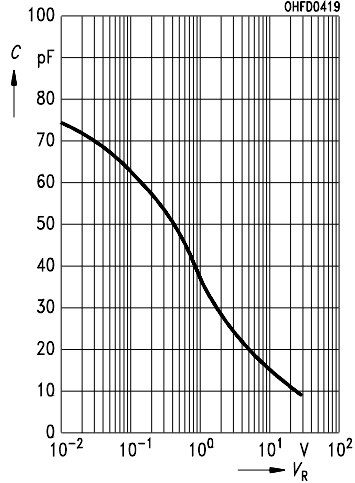
**Dark Current**

$I_R = f(V_R), E = 0$



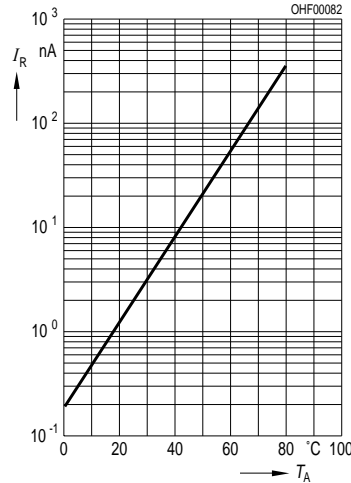
**Capacitance**

$C = f(V_R), f = 1 MHz, E = 0$



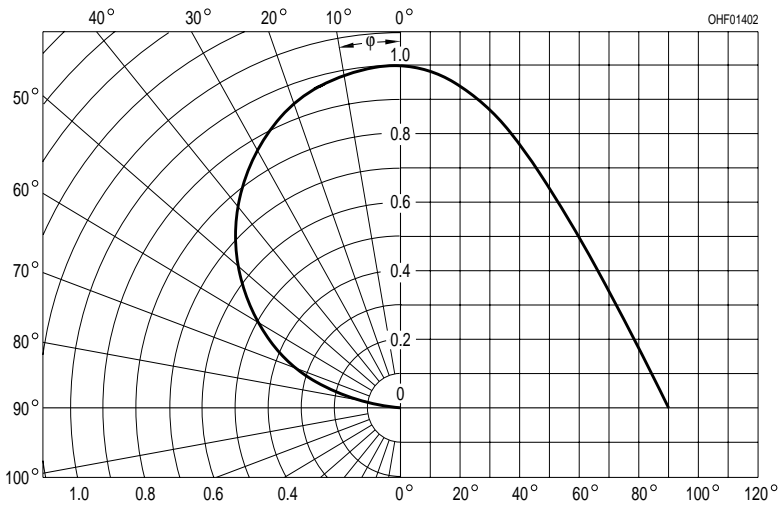
**Dark Current**

$I_R = f(T_A), V_R = 10 V, E = 0$

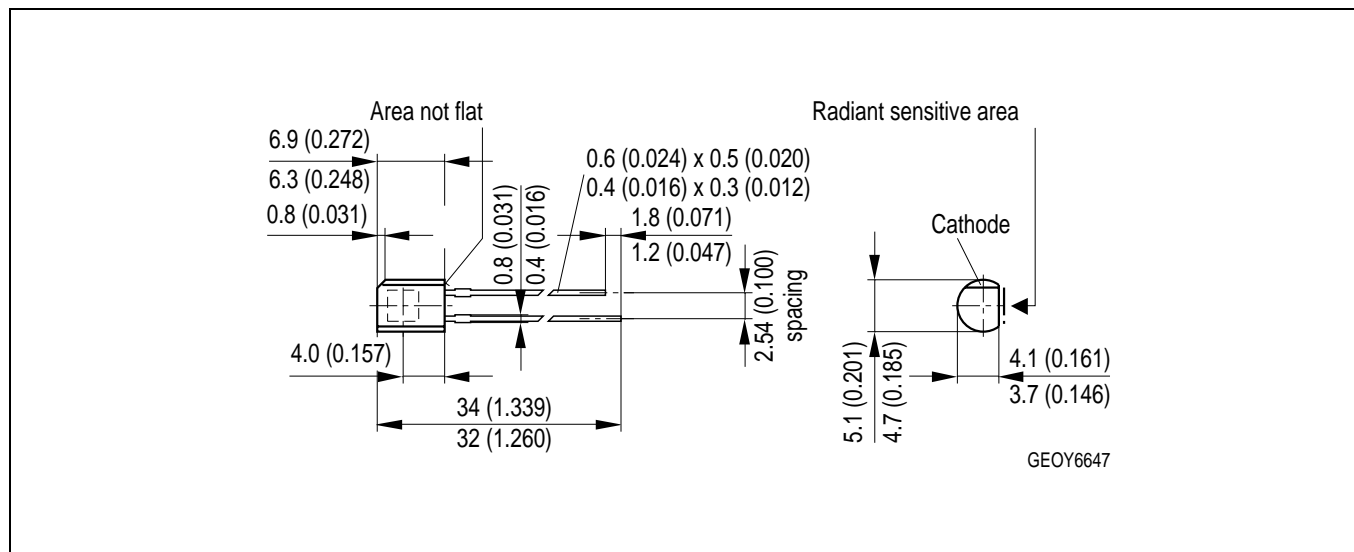


**Directional Characteristics**

$S_{rel} = f(\varphi)$



## Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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### Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

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